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"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

Details

Product Status	Active
Core Processor	e200z0h
Core Size	32-Bit Single-Core
Speed	64MHz
Connectivity	CANbus, I ² C, LINbus, SCI, SPI
Peripherals	DMA, POR, PWM, WDT
Number of I/O	121
Program Memory Size	768KB (768K x 8)
Program Memory Type	FLASH
EEPROM Size	64K x 8
RAM Size	64K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 15x10b, 5x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	144-LQFP
Supplier Device Package	144-LQFP (20x20)
Purchase URL	https://www.e-xfl.com/product-detail/nxp-semiconductors/spc5605bk0vlq6r

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1.3 Device comparison

Table 1 summarizes the functions of the blocks present on the MPC5606BK.

	Table 1.	MPC5606BK	family	compa	arison ¹
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Feature		MPC5605BK		MPC5606BK					
Package	100 LQFP	144 LQFP	176 LQFP	100 LQFP	144 LQFP	176 LQFP			
CPU	e200z0h								
Execution speed ²		Up to 64 MHz							
Code flash memory		768 KB			1 MB				
Data flash memory			64 (4 x	16) KB					
SRAM		64 KB			80 KB				
MPU			8-e	ntry					
eDMA			16	ch					
10-bit ADC			Ye	es					
dedicated ³	7 ch	15 ch	29 ch	7 ch	15 ch	29 ch			
shared with 12-bit ADC	19 ch								
12-bit ADC			Ye	es					
dedicated ⁴			5	ch					
shared with 10-bit ADC	19 ch								
Total timer I/O ⁵	37 ch,	37 ch, 64 ch,			37 ch, 64 ch,				
	16-Dit	16	-Dit	16-Dit	16	-Dit			
			10	cn					
		_	7	ch					
O(I)PWM / ICOC [®]	7 ch			14 ch					
OPWM / ICOC*	13 ch			33 ch	-				
SCI (LINFlex)	4	6	8	4	6	8			
SPI (DSPI)	3	5	6	3	5	6			
CAN (FlexCAN)	6								
1 ² C	1								
32 KHz oscillator			Ye	es	T	r			
GPIO ¹⁰	77	121	149	77	121	149			
Debug	JTAG								

¹ Feature set dependent on selected peripheral multiplexing; table shows example.

² Based on 125 °C ambient operating temperature.

³ Not shared with 12-bit ADC, but possibly shared with other alternate functions.

⁴ Not shared with 10-bit ADC, but possibly shared with other alternate functions.

⁵ Refer to eMIOS section of device reference manual for information on the channel configuration and functions.

⁶ Each channel supports a range of modes including Modulus counters, PWM generation, Input Capture, Output Compare.

⁷ Each channel supports a range of modes including PWM generation with dead time, Input Capture, Output Compare.

⁸ Each channel supports a range of modes including PWM generation, Input Capture, Output Compare, Period and Pulse width measurement.

⁹ Each channel supports a range of modes including PWM generation, Input Capture, and Output Compare.

¹⁰ Maximum I/O count based on multiplexing with peripherals.



1.4 Block diagram

Figure 1 shows a top-level block diagram of the MPC5606BK.



Figure 1. MPC5606BK block diagram



Port	PCR	PCR Alternate		pe ²	₽.°.	Pi	Pin number			
pin	register	function ¹	Function	Periph	I/O direct	Pad ty	RESE config	100 LQFP	144 LQFP	176 LQFP
PA[7]	PCR[7]	AF0 AF1 AF2 AF3	GPIO[7] E0UC[7] LIN3TX —	SIUL eMIOS_0 LINFlex_3	I/O I/O O	J	Tristate	71	104	128
			EIRQ[2] ADC1_S[1]	SIUL ADC_1						
PA[8]	PCR[8]	AF0 AF1 AF2 AF3	GPIO[8] E0UC[8] E0UC[14] —	SIUL eMIOS_0 eMIOS_0 —	I/O I/O I/O	S	Input, weak pull-up	72	105	129
		 N/A ⁶	EIRQ[3] ABS[0] LIN3RX	SIUL BAM LINFlex_3	 					
PA[9]	PCR[9]	AF0 AF1 AF2 AF3 N/A ⁶	GPIO[9] E0UC[9] — CS2_1 FAB	SIUL eMIOS_0 DSPI_1 BAM	I/O I/O — 0 I	S	Pull- down	73	106	130
PA[10]	PCR[10]	AF0 AF1 AF2 AF3 —	GPIO[10] E0UC[10] SDA LIN2TX ADC1_S[2]	SIUL eMIOS_0 I ² C_0 LINFlex_2 ADC_1	I/O I/O I/O O I	J	Tristate	74	107	131
PA[11]	PCR[11]	AF0 AF1 AF2 AF3	GPIO[11] E0UC[11] SCL	SIUL eMIOS_0 I ² C_0	I/O I/O I/O	J	Tristate	75	108	132
			EIRQ[16] LIN2RX ADC1_S[3]	SIUL LINFlex_2 ADC_1						
PA[12]	PCR[12]	AF0 AF1 AF2 AF3 —	GPIO[12] CS3_1 EIRQ[17] SIN_0	SIUL eMIOS_0 DSPI_1 SIUL DSPI_0	I∕O ∕O	S	Tristate	31	45	53
PA[13]	PCR[13]	AF0 AF1 AF2 AF3	GPIO[13] SOUT_0 E0UC[29] —	SIUL DSPI_0 eMIOS_0 —	I/O O I/O —	М	Tristate	30	44	52
PA[14]	PCR[14]	AF0 AF1 AF2 AF3 —	GPIO[14] SCK_0 CS0_0 E0UC[0] EIRQ[4]	SIUL DSPI_0 DSPI_0 eMIOS_0 SIUL	I/O I/O I/O I	М	Tristate	28	42	50

Table 2.	Functional	port pi	ins (continued)
		P • • • P		



Port	PCR	Alternate		eral	ion	pe ²	ЕТ g. ³	Pi	in numb	er
pin	register	function ¹	Function	Periph	I/O direct	Pad ty	RESE confi	100 LQFP	144 LQFP	176 LQFP
PE[14]	PCR[78]	AF0 AF1 AF2 AF3 —	GPIO[78] SCK_2 E1UC[21] — EIRQ[12]	SIUL DSPI_2 eMIOS_1 — SIUL	I/O I/O I/O I	S	Tristate	_	112	136
PE[15]	PCR[79]	AF0 AF1 AF2 AF3	GPIO[79] CS0_2 E1UC[22] —	SIUL DSPI_2 eMIOS_1 —	I/O I/O I/O	М	Tristate		113	137
				Port F						
PF[0]	PCR[80]	AF0 AF1 AF2 AF3 —	GPIO[80] E0UC[10] CS3_1 — ADC0_S[8]	SIUL eMIOS_0 DSPI_1 ADC_0	I/O I/O O I	J	Tristate		55	63
PF[1]	PCR[81]	AF0 AF1 AF2 AF3 —	GPIO[81] E0UC[11] CS4_1 ADC0_S[9]	SIUL eMIOS_0 DSPI_1 ADC_0	I/O I/O O I	J	Tristate		56	64
PF[2]	PCR[82]	AF0 AF1 AF2 AF3 —	GPIO[82] E0UC[12] CS0_2 — ADC0_S[10]	SIUL eMIOS_0 DSPI_2 — ADC_0	I/O I/O O I	J	Tristate		57	65
PF[3]	PCR[83]	AF0 AF1 AF2 AF3 —	GPIO[83] E0UC[13] CS1_2 — ADC0_S[11]	SIUL eMIOS_0 DSPI_2 — ADC_0	I/O I/O O I	J	Tristate	_	58	66
PF[4]	PCR[84]	AF0 AF1 AF2 AF3 —	GPIO[84] E0UC[14] CS2_2 — ADC0_S[12]	SIUL eMIOS_0 DSPI_2 — ADC_0	I/O I/O O I	J	Tristate	_	59	67
PF[5]	PCR[85]	AF0 AF1 AF2 AF3 —	GPIO[85] E0UC[22] CS3_2 — ADC0_S[13]	SIUL eMIOS_0 DSPI_2 ADC_0	I/O I/O O I	J	Tristate		60	68
PF[6]	PCR[86]	AF0 AF1 AF2 AF3 —	GPIO[86] E0UC[23] CS1_1 — ADC0_S[14]	SIUL eMIOS_0 DSPI_1 ADC_0	I/O I/O O I	J	Tristate		61	69

 Table 2. Functional port pins (continued)



Port	PCR	Alternate		pheral	ion	'pe²	ЕТ g. ³	Pin number			
pin	register	function ¹	Function	Periph	I/O direct	Pad ty	RESE confi	100 LQFP	144 LQFP	176 LQFP	
PG[7]	PCR[103]	AF0 AF1 AF2 AF3	GPIO[103] E1UC[16] E1UC[30] 	SIUL eMIOS_1 eMIOS_1 	I/O I/O I/O	S	Tristate		29	37	
		_	LIN6RX	WKUP LINFlex_6							
PG[8]	PCR[104]	AF0 AF1 AF2 AF3 —	GPIO[104] E1UC[17] LIN7TX CS0_2 EIRQ[15]	SIUL eMIOS_1 LINFlex_7 DSPI_2 SIUL	I/O I/O I/O I/O	S	Tristate	_	26	34	
PG[9]	PCR[105]	AF0 AF1 AF2 AF3 —	GPIO[105] E1UC[18] SCK_2 WKUP[21] ⁴ LIN7RX	SIUL eMIOS_1 DSPI_2 WKUP LINFlex_7	<u> </u>	S	Tristate		25	33	
PG[10]	PCR[106]	AF0 AF1 AF2 AF3	GPIO[106] E0UC[24] E1UC[31] SIN_4	SIUL eMIOS_0 eMIOS_1 DSPI_4	1/0 1/0 1/0 1	S	Tristate		114	138	
PG[11]	PCR[107]	AF0 AF1 AF2 AF3	GPIO[107] E0UC[25] CS0_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O	М	Tristate		115	139	
PG[12]	PCR[108]	AF0 AF1 AF2 AF3	GPIO[108] E0UC[26] SOUT_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O O	М	Tristate		92	116	
PG[13]	PCR[109]	AF0 AF1 AF2 AF3	GPIO[109] E0UC[27] SCK_4 —	SIUL eMIOS_0 DSPI_4 —	I/O I/O I/O	М	Tristate	_	91	115	
PG[14]	PCR[110]	AF0 AF1 AF2 AF3	GPIO[110] E1UC[0] — —	SIUL eMIOS_1 —	I/O I/O 	S	Tristate	_	110	134	
PG[15]	PCR[111]	AF0 AF1 AF2 AF3 —	GPIO[111] E1UC[1] — —	SIUL eMIOS_1 — —	I/O I/O —	М	Tristate		111	135	
	Port H										

Table 2.	Functional	port pi	ins (continued)
		P • • • P		



Port	PCR	Alternate		eral	ion	pe ²	ET g.3	Pi	in numb	er
pin	register	function ¹	Function	Periph	l/O direct	Pad ty	RESE confiș	100 LQFP	144 LQFP	176 LQFP
PI[14]	PCR[142]	AF0	GPIO[142]	SIUL	I/O	J	Tristate			76
		AF1	—	—	—					
		AF2	—	—	—					
		AF3								
		_	SIN_4	DSPI_4	I					
PI[15]	PCR[143]	AF0	GPIO[143]	SIUL	I/O	J	Tristate	_		75
		AF1	CS0_4	DSPI_4	I/O					
		AF2	—	—	—					
		AF3 —		ADC_0						
	I			Port J		L	I		I	
PJ[0]	PCR[144]	AF0	GPIO[144]	SIUL	I/O	J	Tristate	_		74
- 1 - 1		AF1	CS1_4	DSPI_4	I/O					
		AF2	—	—	—					
		AF3	—	—	—					
		—	ADC0_S[24]	ADC_0	I					
PJ[1]	PCR[145]	AF0	GPIO[145]	SIUL	I/O	J	Tristate	_	_	73
		AF1	—	—	—					
		AF2	—	—	—					
		AF3								
		_	SIN 5	DSPL 5						
D I/O		450		0			Tristata			70
PJ[2]	PCR[146]	ΔF0 ΔF1	GPI0[146]	DSPL 5	1/0	J	Instate	_	_	12
		AF2								
		AF3	_		_					
		—	ADC0_S[26]	ADC_0	Ι					
PJ[3]	PCR[147]	AF0	GPIO[147]	SIUL	I/O	J	Tristate	—	—	71
		AF1	CS1_5	DSPI_5	I/O					
		AF2	—	—	—					
		AF3 —		ADC_0						
PJ[4]	PCR[148]	AF0	GPI0[148]	SIUL	I/O	М	Tristate			5
		AF1	SCK 5	DSPI 5	I/O					Ŭ
		AF2	E1UC[18]	eMIOS_1	—					
		AF3	—	—	—					

 Table 2. Functional port pins (continued)

¹ Alternate functions are chosen by setting the values of the PCR.PA bitfields inside the SIUL module. PCR.PA = 00 → AF0; PCR.PA = 01 → AF1; PCR.PA = 10 → AF2; PCR.PA = 11 → AF3. This is intended to select the output functions; to use one of the input functions, the PCR.IBE bit must be written to '1', regardless of the values selected in the PCR.PA bitfields. For this reason, the value corresponding to an input only function is reported as "—".

² See Table 3.

³ The RESET configuration applies during and after reset.



3.5 Thermal characteristics

3.5.1 External ballast resistor recommendations

External ballast resistor on V_{DD_BV} pin helps in reducing the overall power dissipation inside the device. This resistor is required only when maximum power consumption exceeds the limit imposed by package thermal characteristics.

As stated in Table 11 LQFP thermal characteristics, considering a thermal resistance of 144 LQFP as 48.3 °C/W, at ambient temperature $T_A = 125$ °C, the junction temperature T_j will cross 150 °C if the total power dissipation is greater than (150 - 125)/48.3 = 517 mW. Therefore, the total device current I_{DDMAX} at 125 °C/5.5 V must not exceed 94.1 mA (i.e., PD/VDD). Assuming an average $I_{DD}(V_{DD_{-HV}})$ of 15–20 mA consumption typically during device RUN mode, the LV domain consumption $I_{DD}(V_{DD_{-BV}})$ is thus limited to $I_{DDMAX} - I_{DD}(V_{DD_{-HV}})$, i.e., 80 mA.

Therefore, respecting the maximum power allowed as explained in Section 3.5.2, Package thermal characteristics, it is recommended to use this resistor only in the 125 °C/5.5 V operating corner as per the following guidelines:

- If $I_{DD}(V_{DD BV}) < 80$ mA, then no resistor is required.
- If 80 mA < I_{DD}(V_{DD BV}) < 90 mA, then 4 Ω resistor can be used.
- If $I_{DD}(V_{DD BV}) > 90$ mA, then 8 Ω resistor can be used.

Using resistance in the range of 4–8 Ω , the gain will be around 10–20% of total consumption on V_{DD_BV}. For example, if 8 Ω resistor is used, then power consumption when I_{DD}(V_{DD_BV}) is 110 mA is equivalent to power consumption when I_{DD}(V_{DD_BV}) is 90 mA (approximately) when resistor not used.

In order to ensure correct power up, the minimum V_{DD_BV} to be guaranteed is 30 ms/V. If the supply ramp is slower than this value, then LVDHV3B monitoring ballast supply V_{DD_BV} pin gets triggered leading to device reset. Until the supply reaches certain threshold, this low voltage monitor generates destructive reset event in the system. This threshold depends on the maximum $I_{DD}(V_{DD_BV})$ possible across the external resistor.

3.5.2 Package thermal characteristics

Table 11. LQFP thermal characteristics¹

Symbol		<u>ر</u>	Parameter	Conditions ²	Pin count)	Unit					
Synn	101	C							Fin count	Min	Тур	Max	Unit
R_{\thetaJA}	СС	D	Thermal resistance,	Single-layer board — 1s	100	—		64	°C/W				
			junction-to-ambient natural convection ³		144	—		64					
				176	—		64						
				Four-layer board — 2s2p	100	—		49.7					
					144	—		48.3					
					176	—		47.3					
$R_{\theta JB}$	СС		Thermal resistance,	Single-layer board — 1s	100	—	_	36	°C/W				
			junction-to-board*		144	—		38					
					176	—	_	38					
				Four-layer board —	100	—	_	33.6					
				2s2p	144	—	—	33.4					
					176	—	—	33.4					



Symbol		C	Parameter	Conditions ²	Pin count		•	Unit	
- Cynn				Conditione		Min	Тур	Max	onit
R_{\thetaJC}	СС		Thermal resistance,	Single-layer board — 1s	100	_	_	23	°C/W
			Junction-to-case [°]		144	_	_	23	
					176			23	
				Four-layer board —	100			19.8	
				2s2p	144			19.2	
					176	_	—	18.8	

Table 11. LQFP thermal characteristics ¹	(continued)
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¹ Thermal characteristics are targets based on simulation.

² $V_{DD} = 3.3 \text{ V} \pm 10\% / 5.0 \text{ V} \pm 10\%$, $T_A = -40$ to 125 °C.

- ³ Junction-to-ambient thermal resistance determined per JEDEC JESD51-3 and JESD51-6. Thermal test board meets JEDEC specification for this package. When Greek letters are not available, the symbols are typed as R_{thJA} and R_{thJMA}.
- ⁴ Junction-to-board thermal resistance determined per JEDEC JESD51-8. Thermal test board meets JEDEC specification for the specified package. When Greek letters are not available, the symbols are typed as R_{th.IB}.
- ⁵ Junction-to-case at the top of the package determined using MIL-STD 883 Method 1012.1. The cold plate temperature is used for the case temperature. Reported value includes the thermal resistance of the interface layer. When Greek letters are not available, the symbols are typed as R_{thJC}.

3.5.3 Power considerations

The average chip-junction temperature, T_J, in degrees Celsius, may be calculated using Equation 1:

$$T_{J} = T_{A} + (P_{D} \times R_{\theta JA})$$
 Eqn. 1

Where:

 T_A is the ambient temperature in °C.

 $R_{\theta JA}$ is the package junction-to-ambient thermal resistance, in °C/W.

 P_D is the sum of P_{INT} and $P_{I/O} (P_D = P_{INT} + P_{I/O})$.

P_{INT} is the product of I_{DD} and V_{DD}, expressed in watts. This is the chip internal power.

 $P_{I/O}$ represents the power dissipation on input and output pins; user determined.

Most of the time for the applications, $P_{I/O} < P_{INT}$ and may be neglected. On the other hand, $P_{I/O}$ may be significant, if the device is configured to continuously drive external modules and/or memories.

An approximate relationship between P_D and T_J (if $P_{I/O}$ is neglected) is given by:

Therefore, solving equations 1 and 2:

$$K = P_D x (T_A + 273 °C) + R_{\theta JA} x P_D^2$$
 Eqn. 3

Where:



K is a constant for the particular part, which may be determined from Equation 3 by measuring P_D (at equilibrium) for a known $T_{A.}$ Using this value of K, the values of P_D and T_J may be obtained by solving equations 1 and 2 iteratively for any value of T_A .

3.6 I/O pad electrical characteristics

3.6.1 I/O pad types

The device provides four main I/O pad types depending on the associated alternate functions:

- Slow pads are the most common pads, providing a good compromise between transition time and low electromagnetic emission.
- Medium pads provide transition fast enough for the serial communication channels with controlled current to reduce electromagnetic emission.
- Fast pads provide maximum speed. These are used for improved debugging capability.
- Input only pads are associated with ADC channels and 32 kHz low power external crystal oscillator providing low input leakage.

Medium and Fast pads can use slow configuration to reduce electromagnetic emission, at the cost of reducing AC performance.

3.6.2 I/O input DC characteristics

Table 12 provides input DC electrical characteristics as described in Figure 5.



Figure 5. I/O input DC electrical characteristics definition



Svm	Symbol	C	Parameter		Conditions ¹	v		Unit	
Cym		Ŭ	i urumeter		Conditions			Max	onn
V _{OL}	СС	С	Output low level MEDIUM configuration	Push Pull	I _{OL} = 3.8 mA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	_		0.2V _{DD}	V
		Ρ			$I_{OL} = 2 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%, \text{ PAD3V5V} = 0$ (recommended)	_	—	0.1V _{DD}	
		С			$I_{OL} = 1 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%, \text{ PAD3V5V} = 1^2$	_	_	0.1V _{DD}	
		С			I _{OL} = 1 mA, V _{DD} = 3.3 V ± 10%, PAD3V5V = 1 (recommended)	_	—	0.5	
		С			I _{OL} = 100 μA, V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	—		0.1V _{DD}	

Table 15. MEDIUM configuration output buffer electrical characteristics (continued)

 1 V_{DD} = 3.3 V \pm 10% / 5.0 V \pm 10%, T_A = -40 to 125 °C, unless otherwise specified

² The configuration PAD3V5 = 1 when V_{DD} = 5 V is only a transient configuration during power-up. All pads but RESET are configured in input or in high impedance state.

Symt		<u>د</u>	Paramotor		Conditions ¹		Value		Unit
Synn	501	C	Falailletei		Conditions	Min	Тур	Max	Unit
V _{OH}	СС	Ρ	Output high level FAST configuration	Push Pull	$I_{OH} = -14 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%,$ PAD3V5V = 0 (recommended)	0.8V _{DD}			V
		С			$I_{OH} = -7 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%,$ $PAD3V5V = 1^2$	0.8V _{DD}		_	
		С			$I_{OH} = -11 \text{ mA},$ $V_{DD} = 3.3 \text{ V} \pm 10\%,$ PAD3V5V = 1 (recommended)	V _{DD} – 0.8			
V _{OL}	СС	Ρ	Output low level FAST configuration	Push Pull	$I_{OL} = 14 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%,$ PAD3V5V = 0 (recommended)	_	_	0.1V _{DD}	V
		С			$I_{OL} = 7 \text{ mA},$ $V_{DD} = 5.0 \text{ V} \pm 10\%,$ $PAD3V5V = 1^2$	_		0.1V _{DD}	
		С			$I_{OL} = 11 \text{ mA},$ $V_{DD} = 3.3 \text{ V} \pm 10\%,$ PAD3V5V = 1 (recommended)	_	_	0.5	

Table 16. FAST configuration output buffer electrical characteristics

 $\overline{^{1}}$ V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified



Package		Supply segment											
I denage	1	2	3	4	5	6	7	8					
176 LQFP	pin7 – pin27	pin28 – pin57	pin59 – pin85	pin86 – pin123	pin124 – pin150	pin151 – pin6	—	—					
144 LQFP	pin20 – pin49	pin51 – pin99	pin100 – pin122	pin 123 – pin19	—	—	—	_					
100 LQFP	pin16 – pin35	pin37 – pin69	pin70 – pin83	pin84 – pin15	—	—	—	—					

Table 18. I/O supply segments

Table 19. I/O consumption

Symbol		C	Parameter	Condi	tions ¹		Unit		
Symbo		C	Falameter	Condi	uons	Min	Тур	Max	Unit
I _{SWTSLW} ,2	CC	D	Dynamic I/O current for SLOW configuration	C _L = 25 pF	$V_{DD} = 5.0 V \pm 10\%,$ PAD3V5V = 0	—	—	20	mA
					V _{DD} = 3.3 V ± 10%, PAD3V5V = 1			16	
I _{SWTMED} ²	CC	D	Dynamic I/O current for MEDIUM configuration	C _L = 25 pF	V _{DD} = 5.0 V ± 10%, PAD3V5V = 0	_	_	29	mA
					V _{DD} = 3.3 V ± 10%, PAD3V5V = 1			17	
I _{SWTFST} ²	CC	D					110	mA	
					V _{DD} = 3.3 V ± 10%, PAD3V5V = 1			50	
I _{RMSSLW}	СС	D	Root medium square I/O	C _L = 25 pF, 2 MHz	$V_{DD} = 5.0 V \pm 10\%$,	—	—	2.3	mA
			current for SLOW configuration	C _L = 25 pF, 4 MHz	PAD3V5V = 0	—	—	3.2	
				C _L = 100 pF, 2 MHz		—	—	6.6	
				C _L = 25 pF, 2 MHz	$V_{DD} = 3.3 V \pm 10\%$,			1.6	
				C _L = 25 pF, 4 MHz	PAD3V5V = 1	—	_	2.3	
				C _L = 100 pF, 2 MHz		—		4.7	
I _{RMSMED}	СС	D	Root medium square I/O	C _L = 25 pF, 13 MHz	$V_{DD} = 5.0 V \pm 10\%$,		_	6.6	mA
			configuration	C _L = 25 pF, 40 MHz $PAD3V5V = 0$		—	_	13.4	
				C _L = 100 pF, 13 MHz		—	-	18.3	
				C _L = 25 pF, 13 MHz	$V_{DD} = 3.3 V \pm 10\%$,		_	5	
				C _L = 25 pF, 40 MHz		—	—	8.5	
				C _L = 100 pF, 13 MHz		—	—	11	



Symbol		C	Parameter	Conditions ¹			Value			
		Ŭ	i didineter		Min	Тур	Max	Unit		
I _{RMSFST}	СС	D	Root medium square I/O	C _L = 25 pF, 40 MHz	$V_{DD} = 5.0 V \pm 10\%$,	—	—	22	mA	
	curr		configuration $C_{L} = 25 \text{ pF}, 64 \text{ MHz}$ $C_{L} = 100 \text{ pF}, 40 \text{ MHz}$ $C_{L} = 100 \text{ pF}, 40 \text{ MHz}$	C _L = 25 pF, 64 MHz	PAD3V5V = 0	—	—	33		
				—	—	56				
				C _L = 25 pF, 40 MHz	$V_{DD} = 3.3 V \pm 10\%$,	—	—	14		
				C _L = 25 pF, 64 MHz	PAD3V5V = 1	—	—	20		
				C _L = 100 pF, 40 MHz		—	—	35		
I _{AVGSEG}	AVGSEG SR D Sum of all the static I/O current within a supply segment		Sum of all the static I/O	V _{DD} = 5.0 V ± 10%, PA	AD3V5V = 0			70	mA	
			$V_{DD} = 3.3 \text{ V} \pm 10\%, \text{ PA}$	AD3V5V = 1	_	_	65			

Table 19. I/O consumption (continued)

 1 V_{DD} = 3.3 V ± 10% / 5.0 V ± 10%, T_A = -40 to 125 °C, unless otherwise specified

 2 Stated maximum values represent peak consumption that lasts only a few ns during I/O transition.

Table 20 provides the weight of concurrent switching I/Os.

In order to ensure device functionality, the sum of the weight of concurrent switching I/Os on a single segment should remain below the 100%.

Su	innly seam	ent			176 L	.QFP		144/100 LQFP					
	ppiy segm		Pad	Weight 5 V		Weight 3.3 V		Weig	ht 5 V	Weight 3.3 V			
176 LQFP	P 144 LQFP 100 LQFP			$SRC^2 = 0$	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1	SRC = 0	SRC = 1		
6	4	4	PB[3]	5%	—	6%	—	13%	—	15%	_		
			PC[9]	4%	—	5%	—	13%	—	15%	—		
			PC[14]	4%	—	4%	—	13%	—	15%	—		
			PC[15]	3%	4%	4%	4%	12%	18%	15%	16%		
		_	PJ[4]	3%	4%	3%	3%	_	_		_		

Table 20. I/O weight¹



possible, ideally infinite. This capacitor contributes to attenuating the noise present on the input pin; furthermore, it sources charge during the sampling phase, when the analog signal source is a high-impedance source.

A real filter can typically be obtained by using a series resistance with a capacitor on the input pin (simple RC filter). The RC filtering may be limited according to the value of source impedance of the transducer or circuit supplying the analog signal to be measured. The filter at the input pins must be designed taking into account the dynamic characteristics of the input signal (bandwidth) and the equivalent input impedance of the ADC itself.

In fact a current sink contributor is represented by the charge sharing effects with the sampling capacitance: C_S being substantially a switched capacitance, with a frequency equal to the conversion rate of the ADC, it can be seen as a resistive path to ground. For instance, assuming a conversion rate of 1 MHz, with C_S equal to 3 pF, a resistance of 330 k Ω is obtained ($R_{EQ} = 1 / (fc \times C_S)$, where fc represents the conversion rate at the considered channel). To minimize the error induced by the voltage partitioning between this resistance (sampled voltage on C_S) and the sum of $R_S + R_F + R_L + R_{SW} + R_{AD}$, the external circuit must be designed to respect the Equation 4:

$$V_A \bullet \frac{\mathbf{R}_S + \mathbf{R}_F + \mathbf{R}_L + \mathbf{R}_S \mathbf{W} + \mathbf{R}_{AD}}{\mathbf{R}_{EO}} < \frac{1}{2} \text{LSB}$$

EXTERNAL CIRCUIT INTERNAL CIRCUIT SCHEME VDD Channel Sampling Selection Filter **Current Limiter** Source 0 R_{SW1} R_F R 11 ... 11 C 11 11 11 Source Impedance R_S R_F Filter Resistance CF Filter Capacitance R Current Limiter Resistance R_{SW1} Channel Selection Switch Impedance Sampling Switch Impedance Pin Capacitance (two contributions, C_{P1} and C_{P2}) R_{AD} CP Sampling Capacitance

Equation 4 generates a constraint for external network design, in particular on resistive path. Internal switch resistances (R_{SW} and R_{AD}) can be neglected with respect to external resistances.

Figure 18. Input equivalent circuit (precise channels)

Eqn. 4





Figure 19. Input equivalent circuit (extended channels)

A second aspect involving the capacitance network shall be considered. Assuming the three capacitances C_{F} , C_{P1} and C_{P2} are initially charged at the source voltage V_A (refer to the equivalent circuit reported in Figure 18): A charge sharing phenomenon is installed when the sampling phase is started (A/D switch close).



Figure 20. Transient behavior during sampling phase

In particular two different transient periods can be distinguished:

1. A first and quick charge transfer from the internal capacitance C_{P1} and C_{P2} to the sampling capacitance C_S occurs (C_S is supposed initially completely discharged): considering a worst case (since the time constant in reality would be faster) in which C_{P2} is reported in parallel to C_{P1} (call $C_P = C_{P1} + C_{P2}$), the two capacitances C_P and C_S are in series, and the time constant is



Cumh	.1	~	Devementer	Condit	:1		Unit		
Symbo	וע	C	Parameter	Condit	ions	Min	Тур	Max	Onit
R _{SW1}	СС	D	Internal resistance of analog source	_		—	—	3	kΩ
R _{SW2}	СС	D	Internal resistance of analog source	_	-		—	2	kΩ
R _{AD}	СС	D	Internal resistance of analog source		-	_	—	2	kΩ
I _{INJ}	SR		Input current Injection	Current injection $V_{DD} =$ on one ADC_0 3.3 V ± 10%		-5	—	5	mA
				from the converted one	V _{DD} = 5.0 V ± 10%	-5	_	5	
INL	СС	Т	Absolute value for integral nonlinearity	No overload		_	0.5	1.5	LSB
DNL	СС	Т	Absolute differential nonlinearity	No overload		_	0.5	1.0	LSB
OFS	СС	Т	Absolute offset error		-	_	0.5	—	LSB
GNE	СС	Т	Absolute gain error		-	—	0.6	—	LSB
TUEP	СС	Ρ	Total unadjusted error ⁷ for	Without current i	njection	-2	0.6	2	LSB
		Т	precise channels, input only pins	With current injection		-3	—	3	
TUEX	СС	Т	Total unadjusted error ⁷ for	Without current i	Without current injection		1	3	LSB
		Т	extended channel	With current inje	ction	-4		4	

 1 V_{DD} = 3.3 V \pm 10% / 5.0 V \pm 10%, T_A = –40 to 125 °C, unless otherwise specified.

 $^2\,$ Analog and digital V_{SS} **must** be common (to be tied together externally).

³ V_{AINx} may exceed V_{SS_ADC0} and V_{DD_ADC0} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0x3FF.

⁴ Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.

⁵ During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC0_S} . After the end of the sample time t_{ADC0_S} , changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC0_S} depend on programming.

⁶ This parameter does not include the sample time t_{ADC0_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.

⁷ Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.



Symbol	1	C	Parameter	Cor	ditions ¹		Unit		
- Cymbol		U	i di dificter	001	Min	Тур	Max	Onic	
I _{INJ}	SR	—	Input current Injection	Current	$V_{DD} = 3.3 \text{ V} \pm 10\%$	-5	—	5	mA
				injection on one ADC_1 input, different from the converted one	V _{DD} = 5.0 V ± 10%	-5		5	-
	~~	-						•	
INLP	CC	I	Absolute Integral non-linearity-Precise channels	No overload		1	3	LSB	
INLX	СС	Т	Absolute Integral non-linearity-Extended channels	No overload	_	1.5	5	LSB	
DNL	СС	Т	Absolute Differential non-linearity	No overload		_	0.5	1	LSB
OFS	СС	Т	Absolute Offset error		—		2	_	LSB
GNE	СС	Т	Absolute Gain error		—		2	_	LSB
TUEP ⁷	СС	Ρ	Total Unadjusted Error for	Without curren	t injection	-6	—	6	LSB
		Т	precise channels, input only pins	With current in	jection	-8	—	8	
TUEX ⁷	СС	Т	Total Unadjusted Error for	Without current injection		-10	—	10	LSB
		Т	extended channel	With current in	jection	-12	—	12	

Table 42. ADC	1 conversion characteris	stics (12-bit ADC	1) ((continued)

¹ V_{DD} = 3.3 V \pm 10% / 5.0 V \pm 10%, T_A = -40 to 125 °C, unless otherwise specified

² Analog and digital V_{SS} must be common (to be tied together externally).

- ³ V_{AINx} may exceed V_{SS_ADC1} and V_{DD_ADC1} limits, remaining on absolute maximum ratings, but the results of the conversion will be clamped respectively to 0x000 or 0xFFF.
- ⁴ During the sample time the input capacitance C_S can be charged/discharged by the external source. The internal resistance of the analog source must allow the capacitance to reach its final voltage level within t_{ADC1_S}. After the end of the sample time t_{ADC1_S}, changes of the analog input voltage have no effect on the conversion result. Values for the sample clock t_{ADC1_S} depend on programming.
- ⁵ This parameter does not include the sample time t_{ADC1_S}, but only the time for determining the digital result and the time to load the result's register with the conversion result.
- ⁶ Duty cycle is ensured by using system clock without prescaling. When ADCLKSEL = 0, the duty cycle is ensured by internal divider by 2.
- ⁷ Total Unadjusted Error: The maximum error that occurs without adjusting Offset and Gain errors. This error is a combination of Offset, Gain and Integral Linearity errors.



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3.18.2 DSPI characteristics

Table 44. DSPI characteristics¹

Na	Sumb		~	Deremeter		DSPI0/D	SPI1/DS	PI5/DSPI6	C	SPI2/DS	SPI4	l Init
INO.	Symbo	U		Farameter	Min	Тур	Мах	Min	Тур	Мах	Unit	
1	t _{SCK}	SR	D	SCK cycle time	Master mode (MTFE = 0)	125	—		333 ²	—		ns
			D		Slave mode (MTFE = 0)	125	_	_	333		_	
			D		Master mode (MTFE = 1)	83	—	_	125	—		
			D		Slave mode (MTFE = 1)	83	_	_	125	_	_	
_	f _{DSPI}	SR	D	DSPI digital controller fre	quency	—		f _{CPU}	_		f _{CPU}	MHz
2	t _{CSCext} ³	SR	D	CS to SCK delay	Slave mode	32		_	32		—	ns
3	t _{ASCext} ⁴	SR	D	After SCK delay	Slave mode	1/f _{DSPI} + 5	—	_	1/f _{DSPI} + 5	—	_	ns
4	t _{SDC}	CC	D	SCK duty cycle	Master mode	—	t _{SCK} /2	—		t _{SCK} /2	—	ns
		SR	D		Slave mode	t _{SCK} /2	_	_	t _{SCK} /2		—	
5	t _A	SR	D	Slave access time	Slave mode	_		1/f _{DSPI} + 70	_		1/f _{DSPI} + 130	ns
6	t _{DI}	SR	D	Slave SOUT disable time	Slave mode	7	—	_	7	_	_	ns
7	t _{PCSC}	CC	D	PCSx to PCSS time	—	13 ⁵	—	—	13 ⁵	—	—	
8	t _{PASC}	CC	D	PCSS to PCSx time	—	13 ⁵	—	—	13 ⁵	—	—	
9	t _{SUI}	SR	D	Data setup time for	Master mode	43		—	145		—	ns
				inputs	Slave mode	5		_	5		—	
10	t _{HI}	SR	D	Data hold time for inputs	Master mode	0		_	0		—	ns
					Slave mode	2 ⁶	_	—	2 ⁶	_	—	
11	t _{SUO} 7	CC	D	Data valid after SCK	Master mode	—	—	32	_	—	50	ns
				eage	Slave mode	—		52	—		160	





Note: Numbers shown reference Table 44.





Note: Numbers shown reference Table 44.





4 Package characteristics

4.1 Package mechanical data

4.1.1 176 LQFP



Figure 33. 176 LQFP package mechanical drawing (Part 1 of 3)





Figure 34. 176 LQFP package mechanical drawing (Part 2 of 3)